High Current Surface Mount PNP Silicon Low V_{CE(sat)} Transistor for Battery Operated Applications

Features

- High Current Capability (3 A)
- High Power Handling (Up to 650 mW)
- Low V_{CE(s)} (170 mV Typical @ 1 A)
- Small Size
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Benefits

- High Specific Current and Power Capability Reduces Required PCB Area
- Reduced Parasitic Losses Increases Battery Life

MAXIMUM RATINGS (T_A = 25°C)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V _{CEO}	-12	Vdc
Collector-Base Voltage	V_{CBO}	-12	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous – Peak	I _C I _{CM}	-2.0 -3.0	Adc
Electrostatic Discharge	ESD	HBM Class 3 MM Class C	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol Max		Unit
Total Device Dissipation T _A = 25°C	P _D (Note 1)	450	mW
Derate above 25°C		3.6	mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 1)	275	°C/W
Total Device Dissipation T _A = 25°C	P _D (Note 2)	650	mW
Derate above 25°C		5.2	mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 2)	192	°C/W
Thermal Resistance, Junction-to-Lead 6	$R_{ hetaJL}$	105	°C/W
Total Device Dissipation (Single Pulse < 10 sec.)	P _D Single	1.4	V
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

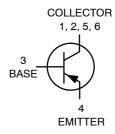
- 1. FR-4, Minimum Pad, 1 oz Coverage
- 2. FR-4, 1" Pad, 1 oz Coverage



ON Semiconductor®

http://onsemi.com

12 VOLTS 3.0 AMPS PNP TRANSISTOR





SC-88/SOT-363 CASE 419B STYLE 20

MARKING DIAGRAM



M = Date Code ■ Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

1

ELECTRICAL CHARACTERISTICS (T₁ = 25°C unless otherwise noted)

ELECTRICAL CHARACTERISTICS (T _J = 25°C unless otherwise noted)					
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector - Emitter Breakdown Voltage, (I _C = -10 mAdc, I _B = 0)	V _{(BR)CEO}	-12	-15	-	Vdc
Collector – Base Breakdown Voltage, (I _C = -0.1 mAdc, I _E = 0)	V _{(BR)CBO}	-12	-25	-	Vdc
Emitter – Base Breakdown Voltage, ($I_E = -0.1 \text{ mAdc}$, $I_C = 0$)	V _{(BR)EBO}	-5.0	-7.0	-	Vdc
Collector Cutoff Current, (V _{CB} = -12 Vdc, I _E = 0)	I _{CBO}	-	-0.02	-0.1	μAdc
Collector–Emitter Cutoff Current, ($V_{CES} = -12 \text{ Vdc}$, $I_E = 0$)	I _{CES}	-	-0.03	-0.1	μAdc
Emitter Cutoff Current, (V _{CES} = -5.0 Vdc, I _E = 0)	I _{EBO}	-	-0.03	-0.1	μAdc
ON CHARACTERISTICS					
DC Current Gain (Note 3) $ (I_C = -0.5 \text{ A, } V_{CE} = -1.5 \text{ V}) $ $ (I_C = -0.8 \text{ A, } V_{CE} = -1.5 \text{ V}) $ $ (I_C = -1.0 \text{ A, } V_{CE} = -1.5 \text{ V}) $	h _{FE}	100 100 100	180 165 160	- 300 -	
Collector – Emitter Saturation Voltage (Note 3) ($I_C = -0.5 \text{ A}$, $I_B = -10 \text{ mA}$) ($I_C = -0.8 \text{ A}$, $I_B = -16 \text{ mA}$) ($I_C = -1.0 \text{ A}$, $I_B = -20 \text{ mA}$)	V _{CE} (sat)	- - -	-0.10 -0.14 -0.17	-0.160 -0.235 -0.290	V
Base – Emitter Saturation Voltage (Note 3) $(I_C = -1.0 \text{ A}, I_B = -20 \text{ mA})$	V _{BE(sat)}	-	-0.84	-0.95	V
Base – Emitter Turn–on Voltage (Note 3) (I _C = -1.0 A, V _{CE} = -1.5 V)	V _{BE(on)}	_	-0.81	-0.95	V
Cutoff Frequency ($I_C = -100 \text{ mA}$, $V_{CE} = -5.0 \text{ V}$, $f = 100 \text{ MHz}$)	f _T	_	100	_	MHz
Output Capacitance (V _{CB} = -1.5 V, f = 1.0 MHz)	C _{obo}	_	50	65	pF

^{3.} Pulsed Condition: Pulse Width < 300 μ sec, Duty Cycle < 2%

ORDERING INFORMATION

Device	Package	Shipping [†]
NSL12AWT1G	SOT-363 (Pb-Free)	3000 Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

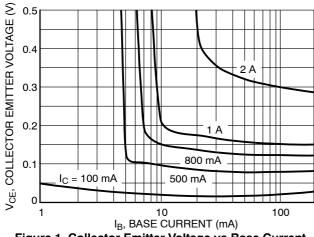


Figure 1. Collector Emitter Voltage vs Base Current

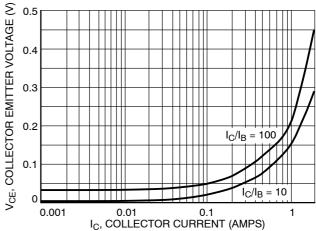


Figure 2. Collector Emitter Voltage vs Collector Current

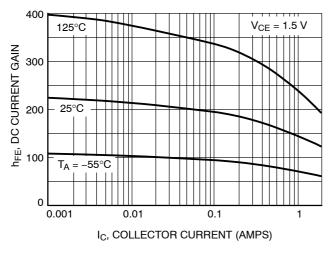


Figure 3. DC Current Gain versus Collector Current

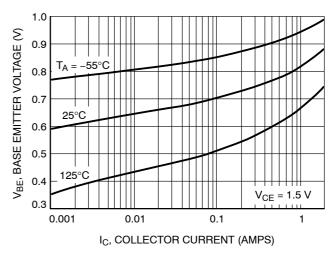


Figure 4. Base Emitter Voltage versus Collector Current

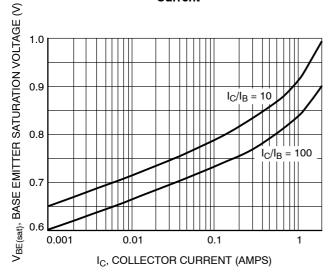


Figure 5. Base Emitter Saturation Voltage versus Base Current

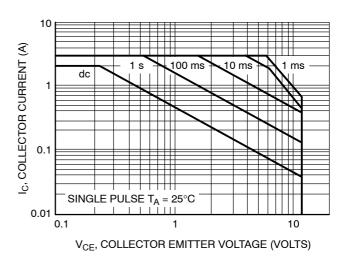


Figure 6. Safe Operating Area

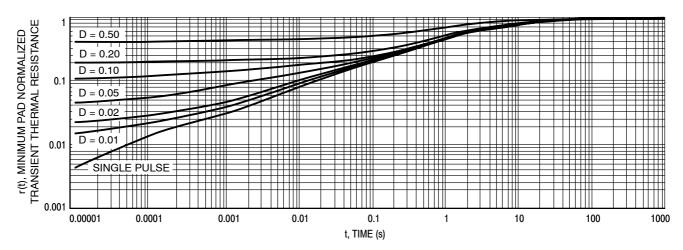
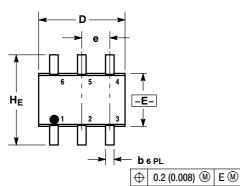


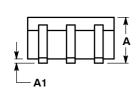
Figure 7. Normalized Thermal Response

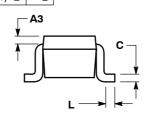
PACKAGE DIMENSIONS

SC-88/SC70-6/SOT-363

CASE 419B-02 **ISSUE W**







- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
- 3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.80	0.95	1.10	0.031	0.037	0.043	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
А3		0.20 REF			0.008 REF		
b	0.10	0.21	0.30	0.004	0.008	0.012	
С	0.10	0.14	0.25	0.004	0.005	0.010	
D	1.80	2.00	2.20	0.070	0.078	0.086	
Е	1.15	1.25	1.35	0.045	0.049	0.053	
е		0.65 BSC		0.026 BSC		С	
L	0.10	0.20	0.30	0.004	0.008	0.012	
HE	2.00	2.10	2.20	0.078	0.082	0.086	

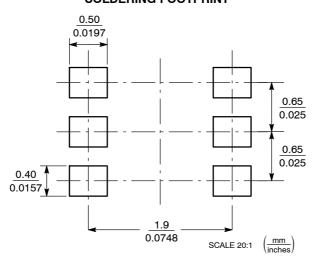
STYLE 20:

PIN 1. COLLECTOR

- 2. COLLECTOR 3. BASE

- 4. EMITTER 5. COLLECTOR
- COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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